

Title (en)

METHOD OF FABRICATING A SEMICONDUCTOR DEVICE

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER HALBLEITERVORRICHTUNG

Title (fr)

PROCEDE DE FABRICATION D'UN DISPOSITIF A SEMI-CONDUCTEUR

Publication

**EP 1185894 A1 20020313 (EN)**

Application

**EP 00937038 A 20000602**

Priority

- GB 0002145 W 20000602
- GB 9913713 A 19990614
- GB 9918097 A 19990803

Abstract (en)

[origin: WO0077548A1] A method of fabricating a semiconductor device includes a step of growing at least one tapered epitaxial layer upon a supporting surface by chemical beam epitaxy, the plane of the taper being inclined to the supporting surface.

IPC 1-7

**G02B 6/132**

IPC 8 full level

**G02B 6/122** (2006.01); **G02B 6/13** (2006.01); **H01L 21/205** (2006.01); **G02B 6/12** (2006.01)

CPC (source: EP)

**G02B 6/1228** (2013.01); **G02B 6/131** (2013.01); **G02B 2006/12078** (2013.01); **H01S 2304/10** (2013.01)

Citation (search report)

See references of WO 0077548A1

Designated contracting state (EPC)

AT BE CH CY DE DK ES FI FR GB GR IE IT LI LU MC NL PT SE

DOCDB simple family (publication)

**WO 0077548 A1 20001221**; AU 5233400 A 20010102; CA 2374942 A1 20001221; CN 1355892 A 20020626; EP 1185894 A1 20020313; JP 2003502844 A 20030121

DOCDB simple family (application)

**GB 0002145 W 20000602**; AU 5233400 A 20000602; CA 2374942 A 20000602; CN 00808830 A 20000602; EP 00937038 A 20000602; JP 2001503549 A 20000602